



## 2-Line Bidirectional ESD Protection Diode

### General description

These dual monolithic silicon surge protection diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment. as computers, printers, business machines, communication systems, medical equipment and other applications. Their bi-directional double ESD design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

### Features and benefits

- Bi-directional ESD protection of 2 lines
- Reverse stand-off voltage: 24.0V Max
- Low clamping voltage
- Low leakage current: nA Level
- Response time is typically < 1 ns
- ESD Protection: 20kV(air)/ 15kV(contact) ( IEC61000-4-2)

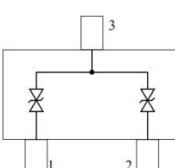
### Application information

- ADAS Control Units CAN Bus
- PowerTrain Control Units
- Electronic Control Units
- Factory Automation
- Body Control Units
- Lightning Control (DALI)

### Ordering information

Device	Package	Marking	Packaging
SM24CN	SOT23	M24C	3000/Tape & Reel

### Schematic & Pin configuration

Circuit diagram	Pinning
	<b>PIN1</b> Lines 1 <b>PIN2</b> Lines 2 <b>PIN3</b> common pin

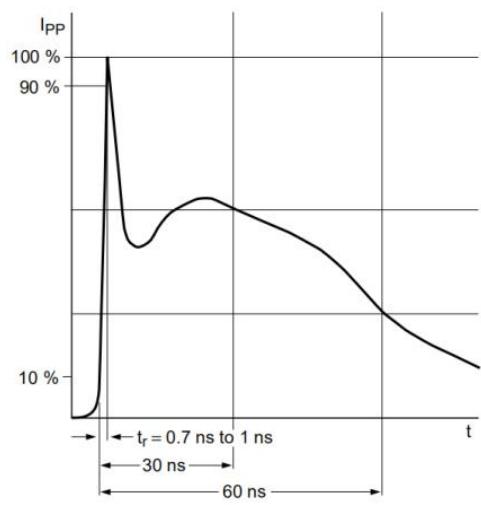
### Maximum Ratings ( $T_{OP} = 25^\circ C$ , unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power ( $tp = 8/20 \mu s$ )	$P_{PPM}$	360	W
Peak Pulse Current( $tp = 8/20 \mu s$ )	$I_{PPM}$	6	A
Maximum lead temperature for soldering during 10s	$T_L$	260	°C
Storage Temperature Range	$T_{stg}$	-55 to +150	°C
Operating Temperature Range	$T_{OP}$	-40 to +125	°C
Maximum junction temperature	$T_j$	150	°C
ESD voltage IEC 61000-4-2 (air discharge)	$V_{ESD}$	20	kV
ESD voltage IEC 61000-4-2 (contact discharge)	$V_{ESD}$	15	kV

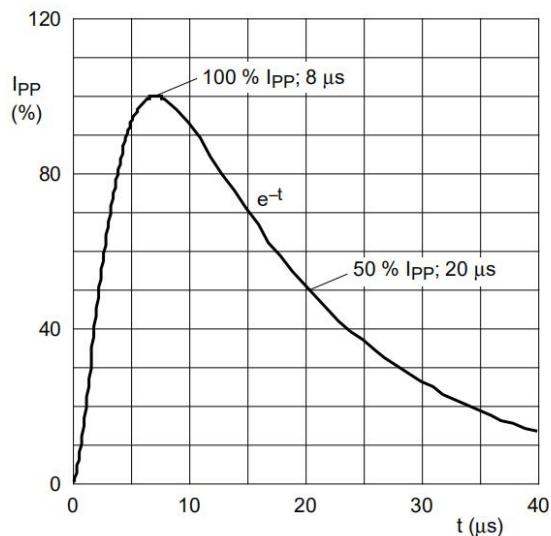
### Electrical Characteristics ( $T_{OP} = 25^\circ C$ , unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Reverse Working Voltage	$V_{RWM}$	--	--	24.0	V	
Breakdown Voltage	$V_{BR}$	26.7	--	--	V	$I_T=1mA$
Leakage Current I <sub>Leak</sub>	$I_R$	--	--	100	nA	$V_{RWM}=24V$
Clamping Voltage	$V_C$	--	--	60.0	V	$I_{PP}=6A, Tp=8/20\mu s$
Junction Capacitance	$C_J$	--	--	20	pF	$V_R=0V, f=1MHz$ (Pin 1 or 2 to 3)

## Typical Characteristics



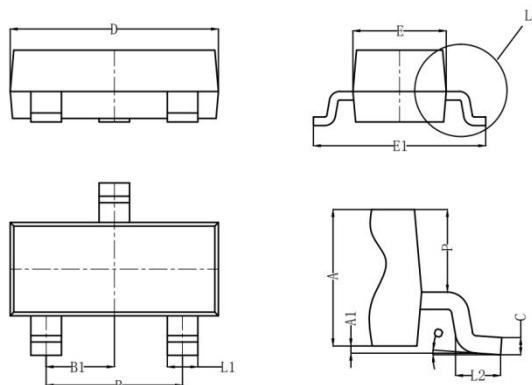
IEC61000-4-2 Waveform



IEC 61000-4-5 Waveform( 8/20 $\mu\text{s}$  pulse)

## Package Outline Dimensions

SOT23



Symbol	Dimensions (mm)		
	Min	Typ	Max
A	0.900	1.000	1.1100
A1	0.000	0.050	0.100
L1	0.350	0.400	0.500
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
B	1.800	1.900	2.000
B1	0.950 Typ		
L2	0.200	0.350	0.450
P	0.550	0.575	0.600